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Team Nexperia

PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 10 — 8 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			PNP	Package
	NXP	JEITA	JEDEC	complement	configuration
PDTC143EE	SOT416	SC-75	-	PDTA143EE	ultra small
PDTC143EM	SOT883	SC-101	-	PDTA143EM	leadless ultra small
PDTC143ET	SOT23	-	TO-236AB	PDTA143ET	small
PDTC143EU	SOT323	SC-70	-	PDTA143EU	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTC143EE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTC143EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTC143ET	-	plastic surface-mounted package; 3 leads	SOT23			
PDTC143EU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC143EE	02
PDTC143EM	E1
PDTC143ET	*02
PDTC143EU	*02

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

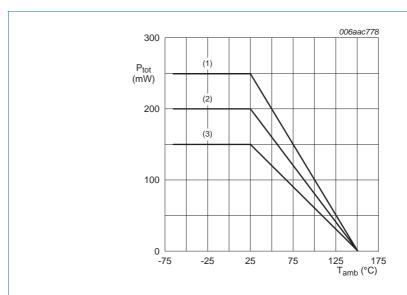
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+30	V
	negative		-	-10	V
I _O	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTC143EE (SOT416)		[1][2]	150	mW
	PDTC143EM (SOT883)		[2][3]	250	mW
	PDTC143ET (SOT23)		[1] -	250	mW
	PDTC143EU (SOT323)		[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

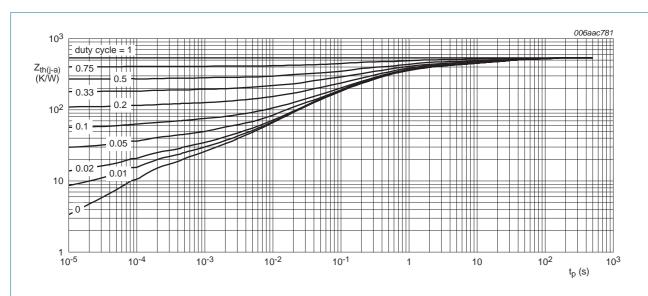
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

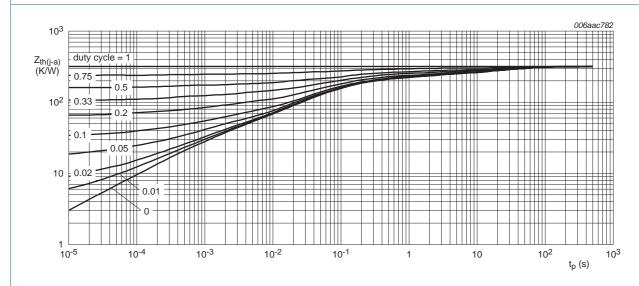
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTC143EE (SOT416)		[1][2]	-	830	K/W
	PDTC143EM (SOT883)		[2][3]	-	500	K/W
	PDTC143ET (SOT23)		[1] -	-	500	K/W
	PDTC143EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



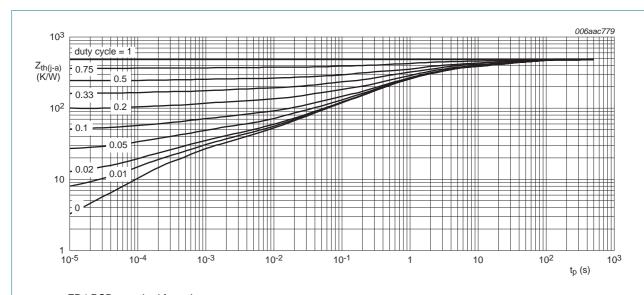
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EE (SOT416); typical values



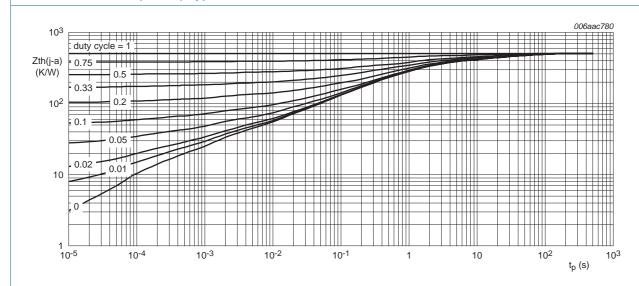
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143ET (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC143EU (SOT323); typical values

NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

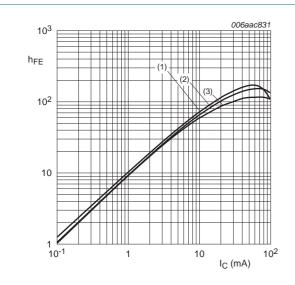
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
cut-	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	900	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2.5	1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1] _	230	-	MHz

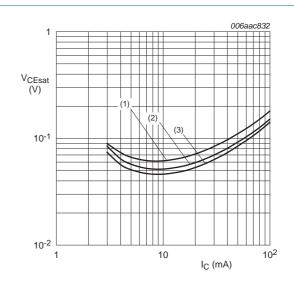
^[1] Characteristics of built-in transistor



$$V_{CE} = 5 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

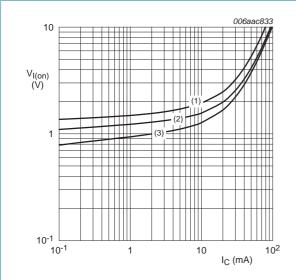
Fig 6. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

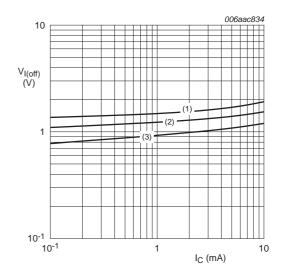
Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 0.3 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

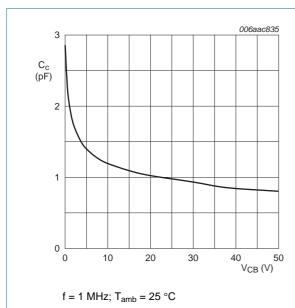


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

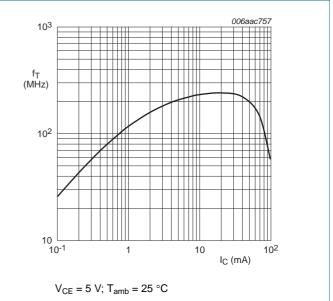


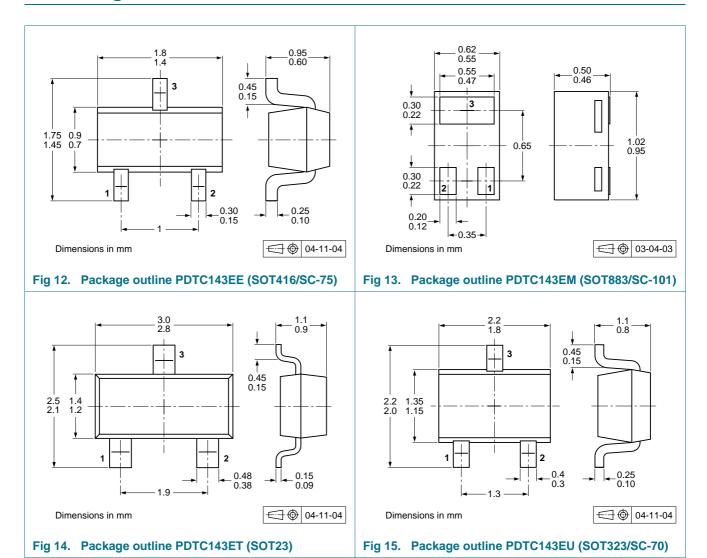
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	5000	10000	
PDTC143EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC143EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC143ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC143EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

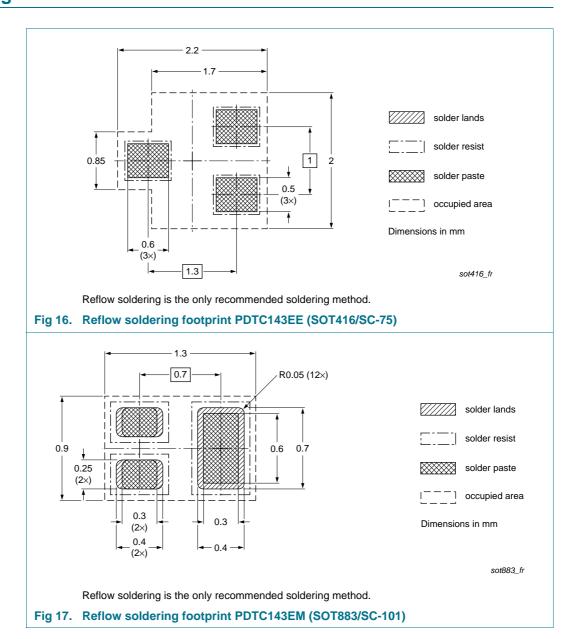
[1] For further information and the availability of packing methods, see Section 14.

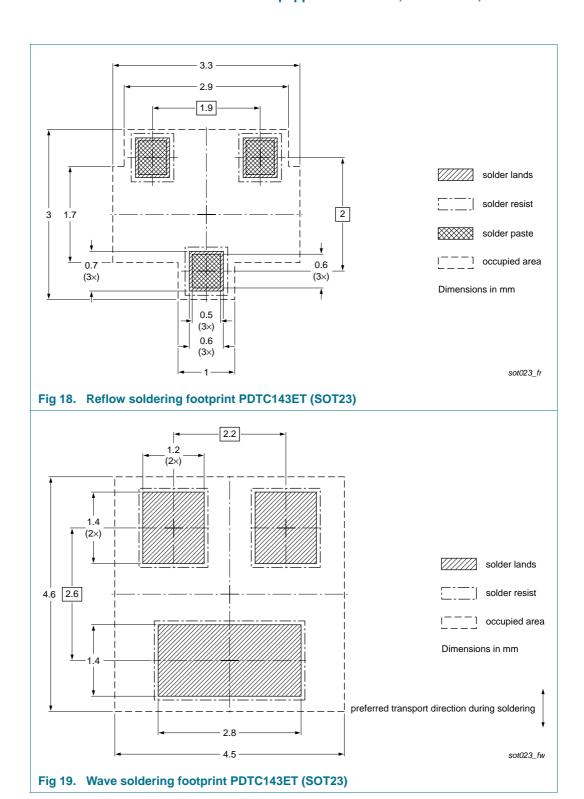
PDTC143E_SER

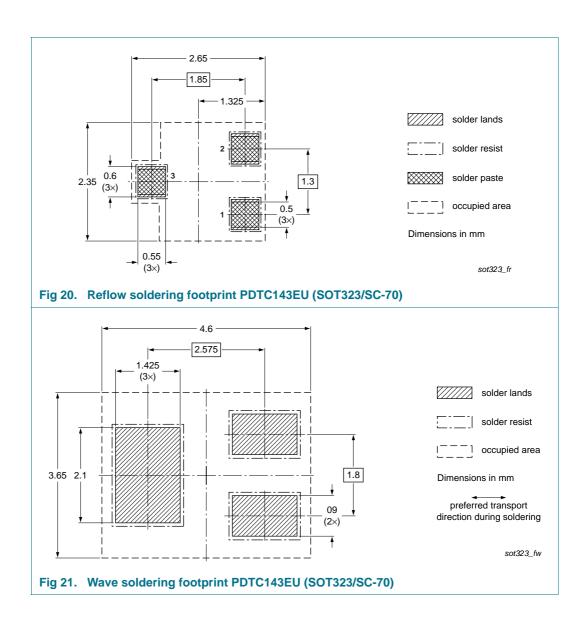
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11. Soldering







NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTC143E_SER v.10	20111208	Product data sheet	-	PDTC143E_SERIES v.9			
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts have been adapted to the new company name where appropriate. 						
	 Type numbers PDTC143EEF, PDTC143EK and PDTC143ES removed. 						
	Section 1 "Product profile": updated						
	Section 4 "Marking": updated						
	• Figure 1 to 11: added						
	Section 6 "Thermal characteristics": updated						
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "Test information": added						
	Section 9 "Package outline": superseded by minimized package outline drawings						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	Section 13 "	Legal information": updated	t				
PDTC143E_SERIES v.9	20040805	Product data sheet	-	PDTC143E_SERIES v.8			
PDTC143E_SERIES v.8	20040318	Product specification	-	PDTC143E_SERIES v.7			
PDTC143E_SERIES v.7	20040112	Product specification	-	PDTC143E_SERIES v.6			
PDTC143E_SERIES v.6	20030910	Product specification	-	PDTC143E_SERIES v.5			
PDTC143E_SERIES v.5	20030410	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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PDTC143E series

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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